

SAM[™] Data Sheet SAM-1150-6-500fs-x, λ = 1150 nm

Laser wavelength	$\lambda = 1150 \text{ nm}$
High reflection band	λ = 1110 1190 nm
Absorptance	A ₀ = 6 %
Saturation fluence	Φ_{sat} = 60 µJ/cm ²
Relaxation time constant	τ ~ 500 fs
Modulation depth	∆R = 3.8 %
Damage threshold	Φ = 900 µJ/cm ²
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 μm
Protection	the SAM is protected with a dielectric front layer
Mounting option x denotes the type of mounting as follows: $\mathbf{x} = 0$ unmounted	
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm \varnothing
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm \oslash

x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm $arnothing$
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm $arnothing$
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm \varnothing

Low intensity spectral reflectance





